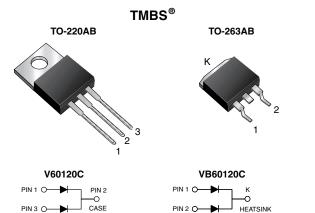
Vishay General Semiconductor

# **Dual High Voltage Trench MOS Barrier Schottky Rectifier**

Ultra Low  $V_F = 0.41$  V at  $I_F = 5$  A



PRIMARY CHARACTERISTICS					
I <sub>F(AV)</sub>	2 x 30 A				
V <sub>RRM</sub>	120 V				
I <sub>FSM</sub>	300 A				
V <sub>F</sub> at I <sub>F</sub> = 30 A	0.71 V				
T <sub>J</sub> max.	150 °C				
Package	TO-220AB, TO-263AB				
Diode variations	Dual common cathode				

### **FEATURES**

- Trench MOS Schottky technology
- · Low forward voltage drop, low power losses
- · High efficiency operation
- Low thermal resistance

## RoHS

- Meets MSL level 1, per J-STD-020, COMPLIANT LF maximum peak of 245 °C (for TO-263AB package)
- Solder bath temperature 275 °C maximum, 10 s, per JESD 22-B106 (for TO-220AB package)
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

### TYPICAL APPLICATIONS

For use in high frequency converters, switching power supplies, freewheeling diodes, OR-ing diode, DC/DC converters and reverse battery protection.

### **MECHANICAL DATA**

Case: TO-220AB and TO-263AB Molding compound meets UL 94 V-0 flammability rating Base P/N-E3 - RoHS-compliant, commercial grade

Terminals: Matte tin plated leads, solderable per J-STD-002 and JESD 22-B102

E3 suffix meets JESD 201 class 1A whisker test

#### Polarity: As marked

Mounting Torque: 10 in-lbs maximum

<b>MAXIMUM RATINGS</b> ( $T_A = 25 \text{ °C}$ unless otherwise noted)							
PARAMETER		SYMBOL	V60120C	VB60120C	UNIT		
Maximum repetitive peak reverse voltage		V <sub>RRM</sub>	120		V		
Maximum average forward rectified current (fig. 1)	per device		60		A		
	per diode	IF(AV)	30				
Peak forward surge current 8.3 ms single half sine-wave superimposed on rated load per diode		I <sub>FSM</sub>	300		А		
Non-repetitive avalanche energy at $T_J = 25 \text{ °C}$ , L = 100 mH per diode		E <sub>AS</sub>	260		mJ		
Peak repetitive reverse current at $t_p = 2 \ \mu s$ , 1 kHz, T <sub>J</sub> = 38 °C ± 2 °C per diode		I <sub>RRM</sub>	0.5		A		
Voltage rate of change (rated V <sub>R</sub> )		dV/dt	10 000		V/µs		
Operating junction and storage temperature range		T <sub>J</sub> , T <sub>STG</sub>	-40 to +150		°C		









www.vishay.com

## Vishay General Semiconductor

<b>ELECTRICAL CHARACTERISTICS</b> ( $T_A = 25 \text{ °C}$ unless otherwise noted)								
PARAMETER	TEST CONDITIONS		SYMBOL	TYP.	MAX.	UNIT		
Breakdown voltage	I <sub>R</sub> = 1.0 mA	T <sub>A</sub> = 25 °C	V <sub>BR</sub>	120 (minimum)	-	V		
Instantaneous forward voltage per diode	I <sub>F</sub> = 5 A	T <sub>A</sub> = 25 °C	– V <sub>F</sub> (1)	0.48	-	V		
	I <sub>F</sub> = 15 A			0.66	-			
	I <sub>F</sub> = 30 A			0.88	0.95			
	I <sub>F</sub> = 5 A	T <sub>A</sub> = 125 °C		0.41	-			
	I <sub>F</sub> = 15 A			0.58	-			
	I <sub>F</sub> = 30 A			0.71	0.75			
Reverse current at rated $V_R$ per diode	V <sub>R</sub> = 90 V	T <sub>A</sub> = 25 °C	I <sub>R</sub> <sup>(2)</sup>	14	-	μA		
		T <sub>A</sub> = 125 °C		11	-	mA		
	V <sub>R</sub> = 120 V	T <sub>A</sub> = 25 °C		40	500	μA		
	$v_{\rm R} = 120$ V	T <sub>A</sub> = 125 °C		15	45	mA		

#### Notes

 $^{(1)}\,$  Pulse test: 300  $\mu s$  pulse width, 1 % duty cycle

<sup>(2)</sup> Pulse test: Pulse width  $\leq$  40 ms

<b>THERMAL CHARACTERISTICS</b> ( $T_A = 25$ °C unless otherwise noted)					
PARAMETER	SYMBOL V60120C		VB60120C	UNIT	
Typical thermal resistance per diode	$R_{ ext{ heta}JC}$	2.2	2.2	°C/W	

ORDERING INFORMATION (Example)						
PACKAGE	PREFERRED P/N	UNIT WEIGHT (g)	PACKAGE CODE	BASE QUANTITY	DELIVERY MODE	
TO-220AB	V60120C-E3/4W	1.89	4W	50/tube	Tube	
TO-263AB	VB60120C-E3/4W	1.38	4W	50/tube	Tube	
TO-263AB	VB60120C-E3/8W	1.38	8W	800/reel	Tape and reel	

## RATINGS AND CHARACTERISTICS CURVES (T<sub>A</sub> = 25 °C unless otherwise noted)

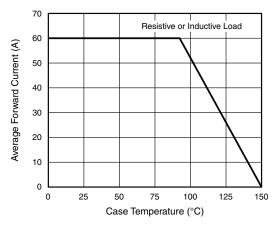


Fig. 1 - Forward Current Derating Curve

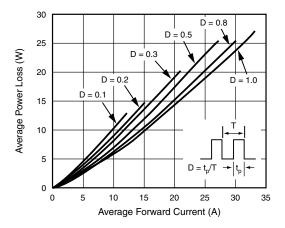


Fig. 2 - Forward Power Loss Characteristics Per Diode



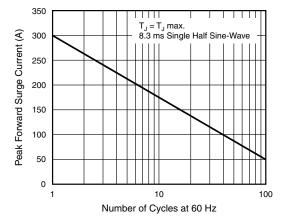


Fig. 3 - Maximum Non-Repetitive Peak Forward Surge Current Per Diode

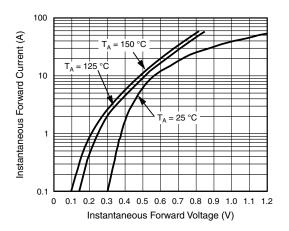


Fig. 4 - Typical Instantaneous Forward Characteristics Per Diode

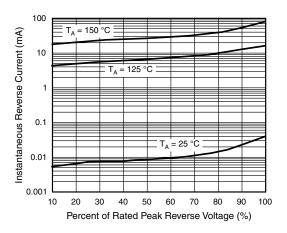


Fig. 5 - Typical Reverse Characteristics Per Diode

## Vishay General Semiconductor

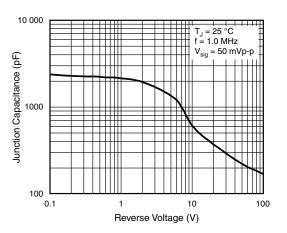


Fig. 6 - Typical Junction Capacitance Per Diode

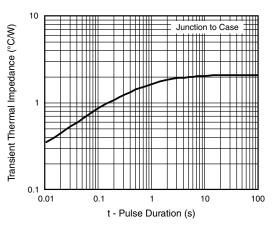


Fig. 7 - Typical Transient Thermal Impedance Per Diode

Revision: 10-May-16

3

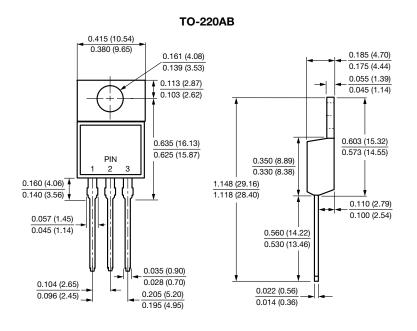
Document Number: 88976

For technical questions within your region: <u>DiodesAmericas@vishay.com</u>, <u>DiodesAsia@vishay.com</u>, <u>DiodesEurope@vishay.com</u> THIS DOCUMENT IS SUBJECT TO CHANGE WITHOUT NOTICE. THE PRODUCTS DESCRIBED HEREIN AND THIS DOCUMENT ARE SUBJECT TO SPECIFIC DISCLAIMERS, SET FORTH AT <u>www.vishay.com/doc?91000</u>

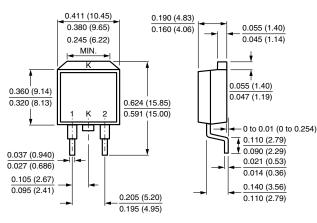
## Vishay General Semiconductor



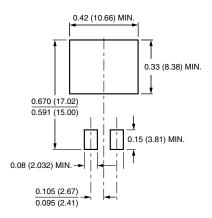
### **PACKAGE OUTLINE DIMENSIONS** in inches (millimeters)



TO-263AB



**Mounting Pad Layout** 





Vishay

## Disclaimer

ALL PRODUCT, PRODUCT SPECIFICATIONS AND DATA ARE SUBJECT TO CHANGE WITHOUT NOTICE TO IMPROVE RELIABILITY, FUNCTION OR DESIGN OR OTHERWISE.

Vishay Intertechnology, Inc., its affiliates, agents, and employees, and all persons acting on its or their behalf (collectively, "Vishay"), disclaim any and all liability for any errors, inaccuracies or incompleteness contained in any datasheet or in any other disclosure relating to any product.

Vishay makes no warranty, representation or guarantee regarding the suitability of the products for any particular purpose or the continuing production of any product. To the maximum extent permitted by applicable law, Vishay disclaims (i) any and all liability arising out of the application or use of any product, (ii) any and all liability, including without limitation special, consequential or incidental damages, and (iii) any and all implied warranties, including warranties of fitness for particular purpose, non-infringement and merchantability.

Statements regarding the suitability of products for certain types of applications are based on Vishay's knowledge of typical requirements that are often placed on Vishay products in generic applications. Such statements are not binding statements about the suitability of products for a particular application. It is the customer's responsibility to validate that a particular product with the properties described in the product specification is suitable for use in a particular application. Parameters provided in datasheets and / or specifications may vary in different applications and performance may vary over time. All operating parameters, including typical parameters, must be validated for each customer application by the customer's technical experts. Product specifications do not expand or otherwise modify Vishay's terms and conditions of purchase, including but not limited to the warranty expressed therein.

Except as expressly indicated in writing, Vishay products are not designed for use in medical, life-saving, or life-sustaining applications or for any other application in which the failure of the Vishay product could result in personal injury or death. Customers using or selling Vishay products not expressly indicated for use in such applications do so at their own risk. Please contact authorized Vishay personnel to obtain written terms and conditions regarding products designed for such applications.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted by this document or by any conduct of Vishay. Product names and markings noted herein may be trademarks of their respective owners.

# **Mouser Electronics**

Authorized Distributor

Click to View Pricing, Inventory, Delivery & Lifecycle Information:

Vishay: <u>V60120C-E3/4W</u> <u>V60120C-E3/45</u>